
2SJ409(L), 2SJ409(S)

Silicon P-Channel MOS FET

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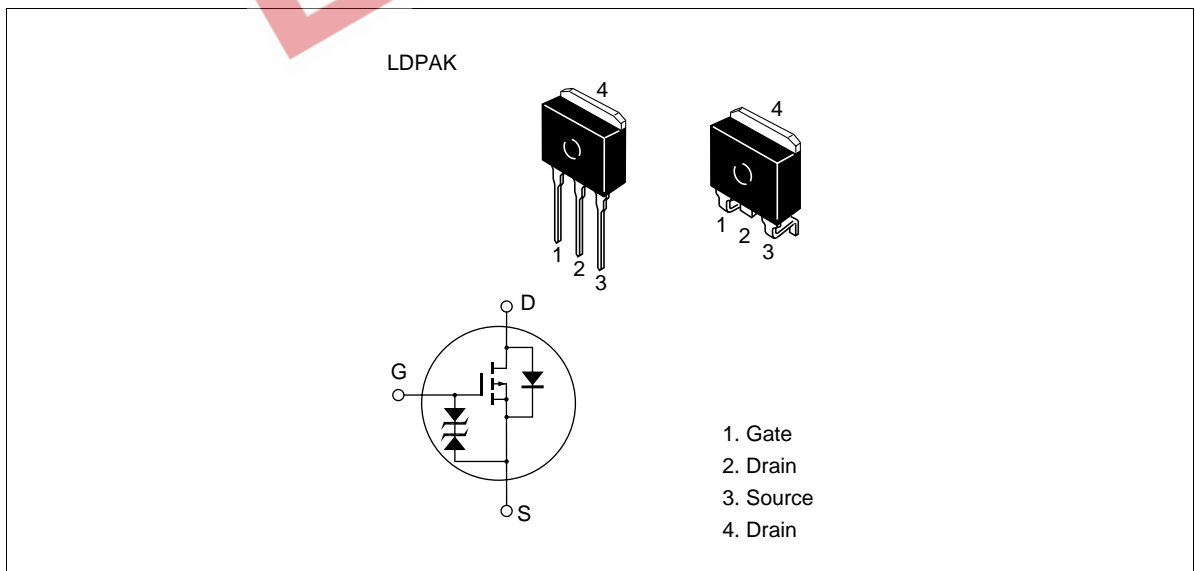
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V Gate drive device can be driven from 5 V source
- Suitable for Switching regulator, DC - DC converter

Outline



2SJ409(L), 2SJ409(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-100	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	-20	A
Drain peak current	$I_{D(pulse)}^{*1}$	-80	A
Body to drain diode reverse drain current	I_{DR}	-20	A
Channel dissipation	P_{ch}^{*2}	75	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ C$

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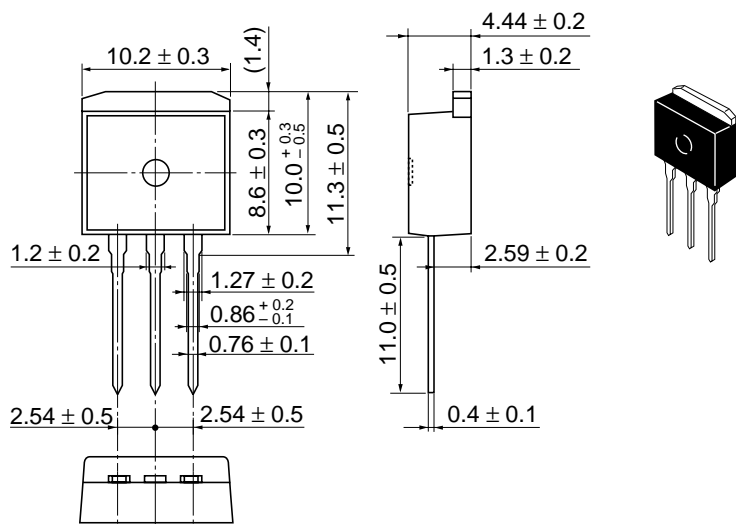
Electrical Characteristics (T_a = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-100	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \text{ } \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-250	μA	$V_{DS} = -80 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.12	0.16	Ω	$I_D = -10 \text{ A}$ $V_{GS} = -10 \text{ V}^{*1}$
			—	0.16	0.22	Ω
Forward transfer admittance	$ y_{fs} $	7.5	12	—	S	$I_D = -10 \text{ A}$ $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	1860	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	C_{oss}	—	680	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	145	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = -10 \text{ A}$
Rise time	t_r	—	115	—	ns	$V_{GS} = -10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	320	—	ns	$R_L = 3 \text{ } \Omega$
Fall time	t_f	—	170	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.05	—	V	$I_F = -20 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	280	—	ns	$I_F = -20 \text{ A}, V_{GS} = 0,$ $diF/dt = 50 \text{ A}/\mu\text{s}$

See characteristics curves of 2SJ221

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Unit: mm



Hitachi Code	LPAK (L)
JEDEC	—
EIAJ	—
Weight (reference value)	1.4 g

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